2SK3036

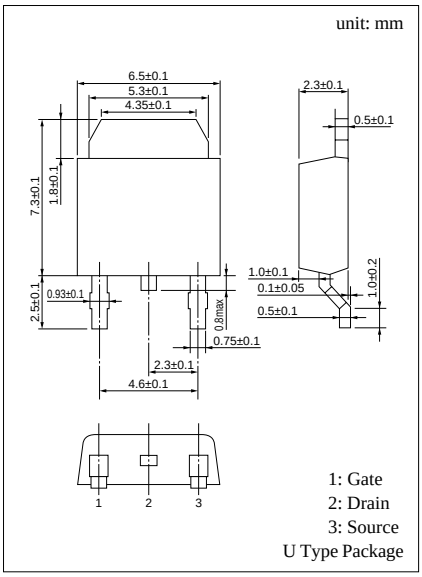
Silicon N-Channel Power F-MOS FET

■ Features

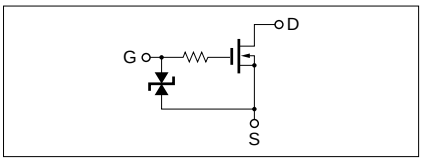
- Avalanche energy capacity guaranteed
- High-speed switching
- Low ON-resistance
- No secondary breakdown
- Low-voltage drive
- High electrostatic breakdown voltage

■ Applications

- Contactless relay
- Diving circuit for a solenoid
- Driving circuit for a motor
- Control equipment
- Switching power supply



Internal Connection



■ Absolute Maximum Ratings (T_C = 25°C)

Parameter		Symbol	Ratings	Unit
Drain to Source breakdown voltage		V_{DSS}	150	V
Gate to Source voltage		V_{GSS}	±20	V
Drain current	DC	I_D	±6	A
	Pulse	I_{DP}	±12	A
Avalanche energy capacity		EAS*	3.6	mJ
Allowable power dissipation	T_C = 25°C	P_D	20	W
	Ta = 25°C		1	
Channel temperature		T_{ch}	150	°C
Storage temperature		T_{stg}	–55 to +150	°C

* L = 0.1mH, I_L = 6A, 1 pulse

■ Electrical Characteristics (T_C = 25°C)

Parameter	Symbol	Conditions	min	typ	max	Unit
Drain to Source cut-off current	I_{DSS}	V_{DS} = 120V, V_{GS} = 0			10	µA
Gate to Source leakage current	I_{GSS}	V_{GS} = ±20V, V_{DS} = 0			±10	µA
Drain to Source breakdown voltage	V_{DSS}	I_D = 1mA, V_{GS} = 0	150			V
Gate threshold voltage	V_{th}	V_{DS} = 10V, I_D = 1mA	1		2.5	V
Drain to Source ON-resistance	$R_{DS(on)1}$	V_{GS} = 10V, I_D = 3A		300	450	mΩ
	$R_{DS(on)2}$	V_{GS} = 4V, I_D = 3A		340	510	mΩ
Forward transfer admittance	$\|Y_{fs}\|$	V_{DS} = 10V, I_D = 3A		4.2		S
Diode forward voltage	V_{DSF}	I_{DR} = 6A, V_{GS} = 0			–1.6	V
Input capacitance (Common Source)	C_{iss}	V_{DS} = 10V, V_{GS} = 0, f = 1MHz		300		pF
Output capacitance (Common Source)	C_{oss}			76		pF
Reverse transfer capacitance (Common Source)	C_{rss}			40		pF
Turn-on time	t_{on}	V_{DD} = 100V, I_D = 3A, V_{GS} = 10V, R_L = 33Ω		80		ns
Turn-off time (delay time)	$t_{d(off)}$			920		ns
Fall time	t_f			250		ns